

IN THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (*Currently Amended*): A method for manufacturing a silicon single-crystal layer comprising:

~~a step for~~ performing a thermal processing operation in which a thermal annealing operation is performed for 1 to 30 seconds time in an atmospheric gas ~~which~~ that is formed by a hydrogen gas, or an inert gas, or a mixture gas of these gases in a temperature of 600 °C to 950 °C.

2. (*Cancelled*).

3. (*Currently Amended*): A method for manufacturing a silicon single-crystal layer according to Claim 1, wherein the silicon single-crystal layer to which the thermal processing operation is performed is formed by a silicon wafer in which an agglutinate ~~which~~ that is cut from an ingot which is formed by a perfect area {P} does not exist under condition that an area is indicated by {H} ~~in which~~ an interstitial silicon [[silicon-type]] point defect exists in an ingot of the silicon single-crystal dominantly, an area is indicated as {V} ~~in which~~ a vacancy [[vacancy-type]] point defect exists dominantly, a perfect area is indicated by {P} ~~in which~~ the agglutinate of the interstitial silicon [[silicon-type]] point defect and the agglutinate of a point defect do not exist.

4. (*Previously Presented*): A method for manufacturing a silicon single-crystal layer according to Claim 1, wherein the thermal processing operation is performed after performing a grinding processing operation for the silicon single-crystal layer.

5. (*Original*): A method for manufacturing a silicon single-crystal layer according to Claim 4 wherein the thermal processing operation is performed at a temperature 600 °C to 800 °C.

6. (*Currently Amended*): A silicon single-crystal layer which is manufactured by a method for manufacturing a silicon single-crystal layer according to Claim 1—~~wherein a quality of a surface is improved by the thermal processing operation.~~